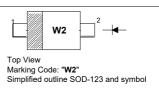


BAS216W Silicon Epitaxial Planar Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25 \circ C$)

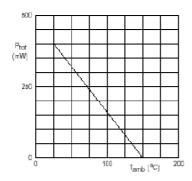
Parameter		Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V _{RRM}	85	V
Reverse Voltage		V_{R}	75	V
Continuous Forward Current		lf	250	mA
Repetitive Peak Forward Current		IFRM	500	mA
Non-repetitive Peak Forward Surge Current	at t = 1 s at t = 1 ms at t = 1 µs	Ігэм	0.5 1 4	А
Power Dissipation		Ptot	400	mW
Junction Temperature		Tj	150	°С
Storage Temperature Range		T_{stg}	- 65 to + 150	°C

Characteristics at $T_a = 25 \, {}_{\circ}C$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1$ mA at $I_F = 10$ mA at $I_F = 50$ mA at $I_F = 150$ mA	VF	0.715 0.855 1 1.25	V
Reverse Current at $V_R = 25 \text{ V}$ at $V_R = 75 \text{ V}$ at $V_R = 25 \text{ V}$, $T_J = 150 _{\circ}\text{C}$ at $V_R = 75 \text{ V}$, $T_J = 150 _{\circ}\text{C}$	I _R	30 1 30 50	nA μA μA μA
Diode Capacitance at $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$	Ctot	1.5	pF
Reverse Recovery Time at I_F = 10 mA to I_R = 10 mA, I_R = 1 mA, R_L = 100 Ω	trr	4	ns

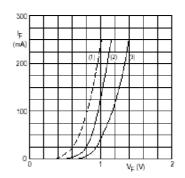


Typical Characteristics



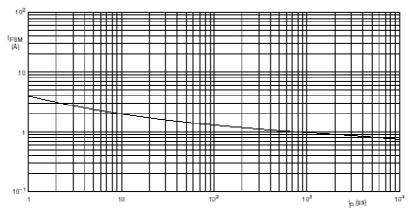
Device mounted on an FR4 printed-circuit board.

Maximum permissible total power dissipation as a function of ambient temperature.



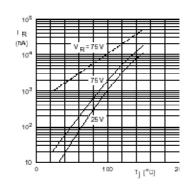
(1) T_j = 158 °C; typical values. (2) T_j = 25 °C; typical values. (3) T_j = 25 °C; maximum values.

Forward current as a function of forward voltage.



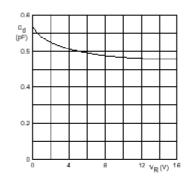
Based on square wave currents. $T_{\rm j} = 25~{\rm ^{1}C}$ prior to surge.

Maximum permissible non-repetitive peak forward current as a function of pulse duration.



Dotted line: maximum values. Solid lines: typical values.

Reverse current as a function of junction temperature.



 $f = 1 \text{ MHz}; T_j = 25 \, ^{\circ}\text{C}.$

6 Diode capacitance as a function of reven voltage; typical values.



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123

